Application No.: 09/784,087 Docket No.: 8733.405.00-US

Amendment dated July 8, 2004

Reply to non-final Office Action dated April 8, 2004

Listing of the Claims

1. (Currently Amended) A liquid crystal display device comprising:

a substrate;

a thin film transistor including a gate electrode, a source electrode, and a drain electrode

on the substrate;

a pixel electrode electrically connected to the drain electrode and in direct contact with

the substrate;

a data line electrically connected with the source electrode;

a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon

layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode; and

a gate pad electrode at one end of the gate line,

wherein the gate pad electrode is formed of a same material and in a same layer as the

pixel electrode in a single layer in direct contact over the first insulating layer,

wherein the first insulating layer includes an opening that exposes a portion of the gate

pad line, and

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad

line and overlaps the first insulating layer.

2. (Original) The device of claim 1, wherein the pixel electrode is selected from a group

consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

3. (Currently Amended) A liquid crystal display device comprising:

a substrate;

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a thin film transistor including a gate electrode, a source electrode, and a drain electrode

on the substrate;

a pixel electrode electrically connected to the drain electrode;

a data line electrically connected with the source electrode;

a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon

layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode; and

a gate pad electrode at one end of the gate line,

wherein the gate pad electrode is formed directly on top of the first insulating layer,

wherein the first insulating layer includes an opening that exposes a portion of the gate

pad line,

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad

line and overlaps the first insulating layer,

wherein the drain electrode has a through hole that exposes a portion of the first

insulating layer, and wherein the pixel electrode electrically contacts an inner side surface of the

drain electrode via the through hole.

4. (Currently Amended) A liquid crystal display device comprising:

a substrate;

a thin film transistor including a gate electrode, a source electrode, and a drain electrode

on the substrate;

a pixel electrode electrically connected to the drain electrode;

a data line electrically connected with the source electrode;

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a first insulating layer, a pure amorphous silicon layer, and a doped amorphous silicon

layer sequentially layered under the data line;

a data pad at one end of the data line;

a gate line electrically connected with the gate electrode;

a gate pad electrode at one end of the gate line; and

a data pad electrode, wherein the data pad has a data pad contact hole passing through the

doped amorphous silicon layer and through the amorphous silicon layer, wherein the data pad

electrode electrically contacts an inner side surface of the data pad via the data pad contact hole,

wherein the gate pad electrode is formed directly on top of the first insulating layer,

wherein the first insulating layer includes an opening that exposes a portion of the gate pad line,

and

wherein the gate pad electrode electrically contacts the exposed portion of the gate pad

line and overlaps the first insulating layer.

5. (Original) The device of claim 4, wherein said data pad electrode is comprised of the

same material as said pixel electrode.

Claims 6-20 (Canceled)

21. (Previously Presented) The device of claim 3, wherein the pixel electrode is selected

from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).

22. (Previously Presented) The device of claim 4, wherein the pixel electrode is selected

from a group consisting of indium tin oxide (ITO) and indium zinc oxide (IZO).